
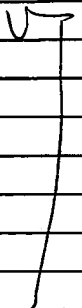
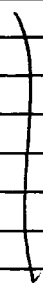
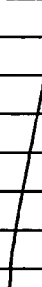



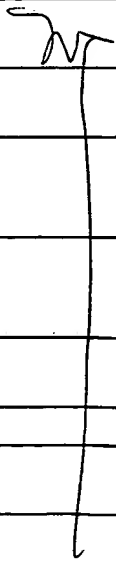
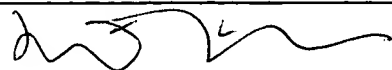

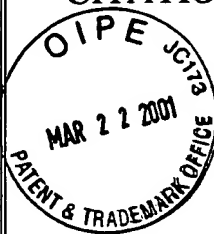
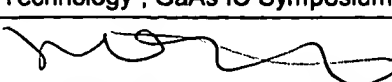

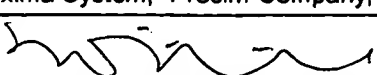


INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 50275-0014		SERIAL NO., 09/675,197	
				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2842 2823	
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	4,812,962	03/14/89	Witt				
	5,051,598	09/24/91	Ashton, et al.				
	5,182,718	01/26/93	Harafugi, et al.				
	5,241,185	08/31/93	Meiri, et al.				
	5,242,770	09/07/93	Chen, et al.				
	5,256,505	10/26/93	Chen, et al.				
	5,316,878	05/31/94	Saito, et al.				
	5,326,659	07/05/94	Liu, et al.				
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	WO 00/67074	11/09/00	PCT			Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	Barouch, E., et al., "OPTIMASK: An OPC Algorithm for Chrome and Phase-Shift Mask Design", 2/22-24/95, SPIE Vol. 2440, pp. 192-206.						
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	Chang, K., et al., "Accurate Modeling of Deep Submicron Interconnect Technology", TMA Times, Fall 1997 Volume IX, No. 3.						
	Cobb, et al., "Fast Sparse Aerial Image Calculation for OPC", SPIE Vol. 2621, pp. 534-544.						
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	Ham, Y. M., et al., "Dependence of Defects in Optical Lithography", Jpn. J. Appl. Phys. Vol. 31 (1992), pp. 4137-4142.						
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

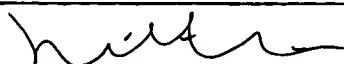
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W	5,340,700	08/23/94	Chen, et al.				
	5,424,154	06/13/95	Borodovsky				
	5,432,714	07/11/95	Chung, et al.				
	5,447,810	09/05/95	Chen, et al.				
	5,533,148	06/02/96	Sayah, et al.				
	5,538,815	07/23/96	Oi, et al.				
	5,553,273	09/03/96	Liebmann				
	5,572,598	11/05/96	Wihl, et al.				
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W	Henke, W., et al., "A Study of Reticle Defects Imaged Into Three-Dimensional Developed Profiles of Positive Photresist Using the SOLID Lithography Simulator", Microelectronic Engineering 14 (1991) 283-297.						
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	Kimura, T., et al., "Subhalf-Micron Gate GaAs Mesfet Process Using Phase-Shifting-Mask Technology", GaAs IC Symposium, 1991, pp. 281-284.						
EXAMINER			DATE CONSIDERED				
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










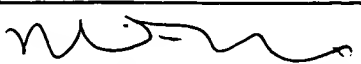

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				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2852 2825	
U.S. PATENT DOCUMENTS							
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W	5,631,110	05/20/97	Shioiri, et al.				
	5,657,235	08/12/97	Liebmann, et al.				
	5,663,893	09/02/97	Wampler, et al.				
	5,702,848	12/30/97	Spence				
	5,705,301	01/06/98	Garza, et al.				
	5,707,765	01/13/98	Chen				
	5,740,068	04/14/98	Liebmann, et al.				
	5,795,688	08/18/98	Burdorf, et al.				
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W	Lithas: Optical Proximity Correction Software						
	MicroUnity: OPC Technology & Product Description, pp. 1-5.						
	Morimoto, H., et al., "Next Generation Mask Strategy-Technologies are Ready for Mass Production of 256MDRAM?", (Panel discussion of PMJ'97 on Apr. 18, 1997), SPIE Vol. 3236 pp. 188-189.						
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	"Proxima System," Precim Company, Portland, Oregon (2 pages).						
EXAMINER 				DATE CONSIDERED 3/20/01			

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				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2842 2825	
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	5,801,954	09/01/98	Le, et al.				
	5,804,340	09/08/98	Garza, et al.				
	5,815,685	09/29/98	Kamon				
	5,825,647	10/20/98	Tsudaka				
	5,827,623	10/27/98	Ishida, et al.				
	5,847,959	12/08/98	Veneklasen, et al.				
	5,849,440	12/15/98	Lucas, et al.				
	5,863,682	01/26/99	Abe, et al.				
	6,081,658	06/27/00	Rieger, et al.				
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EXAMINER 				DATE CONSIDERED 3/2001			

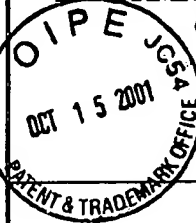
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APPLICANT Christophe Pierrat, et al.							
FILING DATE September 29, 2000						GROUP 2812 2825	
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EXAMINER 				DATE CONSIDERED 			


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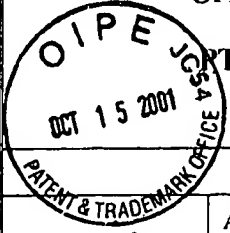


SHEET 1 OF 4

INFORMATION DISCLOSURE CITATION PTO-1449 			ATTY. DOCKET NO. NTI-019-2		SERIAL NO. 09/675,197	
			APPLICANT Pierrat, et al.			
			FILING DATE 9/29/00		GROUP 2812 2825	
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W	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
	4,456,371	6/26/84	Lin	355	71	6/30/82
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
	5,553,274	9/3/96	Liebmann	395	500	6/6/95
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	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95
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	5,885,734	3/23/99	Pierrat, et al.	430	5	8/15/96
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	6,004,702	12/21/99	Lin	430	5	5/21/98
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

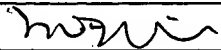
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INFORMATION DISCLOSURE CITATION 	ATTY. DOCKET NO. NTI-019-2	SERIAL NO. 09/675,197
	APPLICANT Pierrat, et al.	
	FILING DATE 9/29/00	GROUP 2812 2825
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
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	APPLICANT Pierrat, et al.	
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INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.

NTI-019-2

Serial No.

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

9/29/2000

Group

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
W	3-80525	4/5/1991	JP - ABSTRACT	X	X	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
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PIERRAT, Christophe

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9/29/2000

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INFORMATION DISCLOSURE CITATION PTO-1449			Atty. Docket No. NTI-019-2		Serial No. 09/675,197	
			Applicant PIERRAT, Christophe		Group <u>2825</u> 2812	
			Filing Date 9/29/2000		RECEIVED AUG. 9 2002 TECHNOLOGY CENTER 2800	
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<u>M</u>	5,991,006	11/23/0199	Tsudaka	355	53	10/27/1997
<u>M</u>	6,243.855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998

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SHEET 2 of 2

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-019-2	Serial No. 09/675,197
		Applicant PIERRAT, Christophe	Group <u>2825</u> 2811
		Filing Date 9/29/2000	
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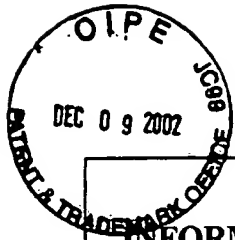
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**INFORMATION DISCLOSURE
CITATION****PTO-1449****Atty. Docket No.**

NTI-019-2

Serial No.

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

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Group

2825

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INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-019-2 Applicant PIERRAT, Christophe Filing Date 9/29/2000	Serial No. 09/675,197 Group 2825
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
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5	Cobb, N., et al., "Fast, Low-Complexity Mask Design", SPIE, Vol. 2440, pp. 313-327, February 22-24, 1995.		
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